

Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

- **Applications**

Inverter, Interface, Driver

- **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on / off conditions need to be set for operation, making the device design easy.

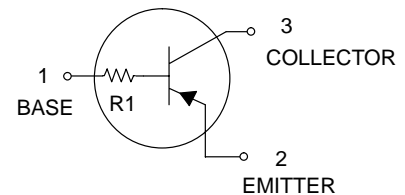
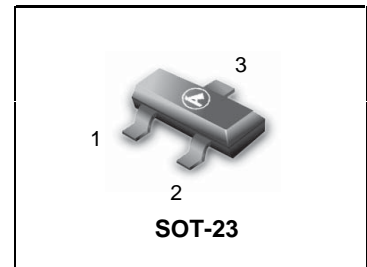
- We declare that the material of product compliance with RoHS requirements.

- S - Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

- **Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	-50	V
Collector-emitter voltage	V _{CE0}	-40	V
Emitter-base voltage	V _{EB0}	-5	V
Collector current	I _c	-500	mA
Collector power dissipation	P _c	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

LDTB114TLT1G
S-LDTB114TLT1G



DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTB114TLT1G S-LDTB114TLT1G	K3	10	—	3000/Tape & Reel
LDTB114TLT3G S-LDTB114TLT3G	K3	10	—	10000/Tape & Reel

- **Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	-50	—	—	V	I _c = -50μA
Collector-emitter breakdown voltage	BV _{CE0}	-40	—	—	V	I _c = -1mA
Emitter-base breakdown voltage	BV _{EB0}	-5	—	—	V	I _E = -50μA
Collector cutoff current	I _{CB0}	—	—	-0.5	μA	V _{CB} = -50V
Emitter cutoff current	I _{EB0}	—	—	-0.5	μA	V _{EB} = -4V
Collector-emitter saturation voltage	V _{CE(sat)}	—	—	-0.3	V	I _c /I _B = -50mA/-2.5mA
DC current transfer ratio	h _{FE}	100	250	600	—	I _c = -50mA, V _{CE} = -5V
Input resistance	R ₁	7	10	13	kΩ	—
Transition frequency	f _t *	—	200	—	MHz	V _{CE} = -10V, I _E =50mA, f=100MHz

* Characteristics of built-in transistor

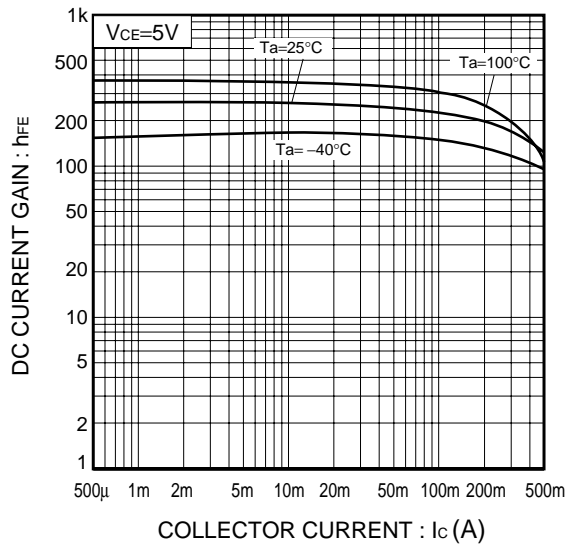
LDTB114TLT1G ; S-LDTB114TLT1G
●Electrical characteristic curves


Fig.1 DC current gain vs. Collector current

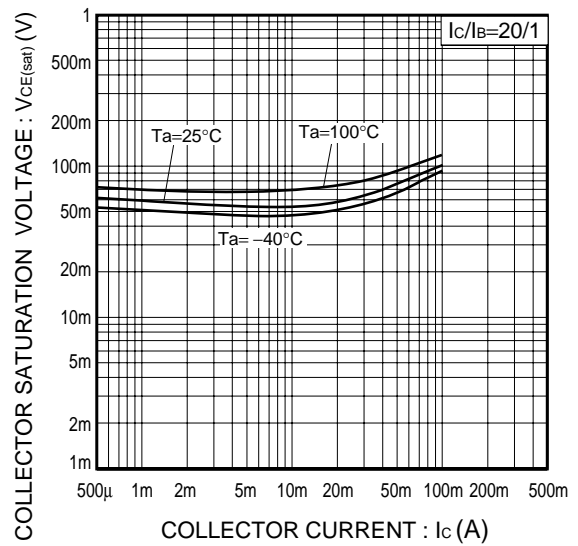


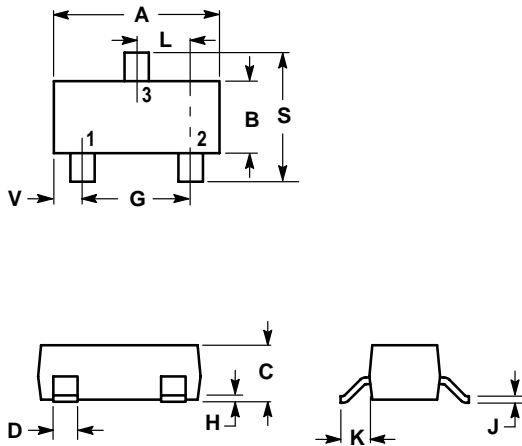
Fig.2 Collector-emitter saturation voltage vs. Collector current

LDTB114TLT1G ; S-LDTB114TLT1G

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

